

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				ATTY DOCKET NO. BUR920010184US	SERIAL NO. 10/695,336	
				Peter J. Geiss et al. FILING 10/28/03	GROUP 2813	
U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
NB		6,294,442	9/2001	Kamal		
NB		5,683,935	11/1997	Miyamoto et al.		
NB		5,385,863	1/1995	Tatsumi et al.		
NB		4,755,476	7/1988	Bohm et al.		
NB		4,467,519	8/1984	Giang et al.		
NB		5,242,844	09/1993	Hayashi		
NB		5,317,432	05/1994	Ino		
NB		6,030,874	02/2000	Grider et al.		
NB		5,254,484	10/1993	Hefner et al.		
NB		5,373,192	12/1994	Eguchi		
NB		5,893,747	04/1999	Yang		
NB		5,744,824	04/1998	Kousai et al.		
NB		6,114,722	09/2000	Jan et al.		
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS
NB		0 521 644	1/1993	EPO		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
		Becker et al., LOW RESISTANCE POLYCRYSTALLINE SILICON BY BORON OR ARSENIC IMPLANTATION AND THERMAL CRYSTALLIZATION OF AMORPHOUSLY DEPOSITED FILMS, J. Appl. Phys., Vol. 56, No. 4, 15 August 1984, pages 1233-1236				
NB		Carbone et al., "Correlation of Ellipsometric Vol. Fraction to Polysilicon Grain Size from Transmission Electron Microscopy", Sept. 1999, IEEE/SEMI Adv. Semiconductor Mfg. Conf. and Workshop, pp. 359-367.				
EXAMINER	Nema Berezny		DATE CONSIDERED		4-16-05	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.